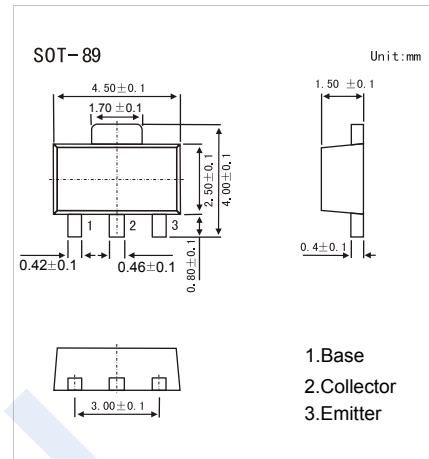


PNP Transistors

2SB1000

■ Features

- Low frequency power amplifier
- Complementary to 2SD1366



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V _{CB0}	-25	V
Collector - Emitter Voltage	V _{CEO}	-20	
Emitter - Base Voltage	V _{EBO}	-5	
Collector Current - Continuous	I _c	-1	A
Collector current -Pulse (Note.1)	I _{CP}	-1.5	
Collector Power Dissipation	P _c	1	W
Junction Temperature	T _J	150	°C
Storage Temperature range	T _{stg}	-55 to 150	

Note.1: PW ≤ 10ms, Duty cycle ≤ 20%

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V _{CB0}	I _c = -100 μA, I _E = 0	-25			V
Collector- emitter breakdown voltage	V _{CEO}	I _c = -1 mA, I _B = 0	-20			
Emitter - base breakdown voltage	V _{EBO}	I _E = -100 μA, I _c = 0	-5			
Collector-base cut-off current	I _{CB0}	V _{CB} = -20V, I _E = 0			-0.1	uA
Emitter cut-off current	I _{EBO}	V _{EB} = -4V, I _c = 0			-0.1	
Collector-emitter saturation voltage	V _{CE(sat)}	I _c = -800 mA, I _B = -80mA		-0.2	-0.3	V
Base - emitter saturation voltage	V _{BE(sat)}	I _c = -800 mA, I _B = -80mA		-0.94	-1.1	
DC current gain	h _{FE}	V _{CE} = -2V, I _c = -500 mA	85		240	
Collector output capacitance	C _{ob}	V _{CB} = -10V, I _E = 0, f = 1MHz		38		pF
Transition frequency	f _T	V _{CE} = -2V, I _c = -500mA		200		MHz

■ Classification of h_{FE}

Type	2SB1000-H	2SB1000-J
Range	85-170	120-240
Marking	AH	AJ

PNP Transistors

2SB1000

■ Typical Characteristics

MAXIMUM COLLECTOR DISSIPATION
CURVE

